

Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low forward voltage drop
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- High frequency switched-mode power supplies

4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _R	reverse voltage	DC		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 73 °C; SQW; <u>Fig. 1;</u> Fig. 2; Fig. 3	[1]	-	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 73 °C; SQW		-	-	16	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; SIN		-	-	60	А
		t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN		-	-	66	А
Static chara	acteristics	·					
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.75	1.95	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.07	1.5	V
		I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>		-	-	1.7	V
Dynamic ch	aracteristics	·					
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _i = 25 °C; <u>Fig. 6</u> ; <u>Fig. 7</u>		-	60	75	ns

[1] Neglecting switching and reverse current losses

5. Pinning information

Table 2. I	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	К — К — А
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYR29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

BYR29X-600

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	600	V
V _{RWM}	crest working reverse voltage			-	600	V
V _R	reverse voltage	DC		-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 73 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 73 °C; SQW		-	16	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN		-	60	А
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN		-	66	А
T _{stg}	storage temperature			-40	150	°C
Tj	junction temperature			-	150	°C

[1] Neglecting switching and reverse current losses

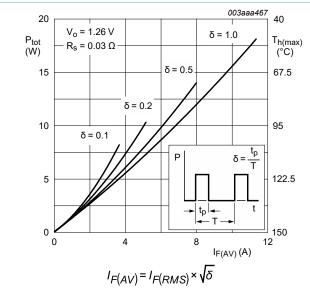


Fig. 1. Forward power dissipation and permissible heatsink temperature as a function of average forward current; square waveform; maximum values

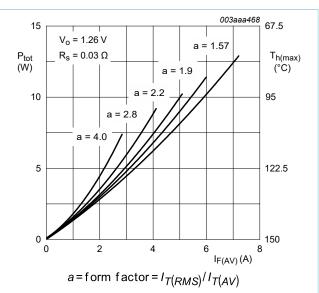
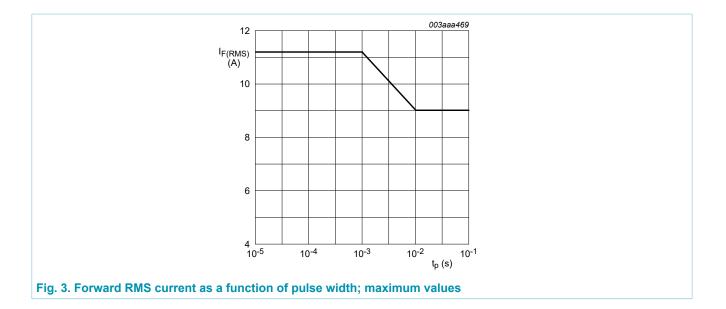


Fig. 2. Forward power dissipation and permissible heatsink temperature as a function of average forward current; sinusoidal waveform; maximum values

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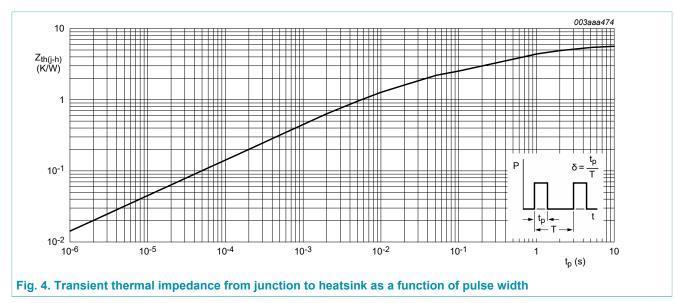


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8. Thermal characteristics

Table 5. Therma	al characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

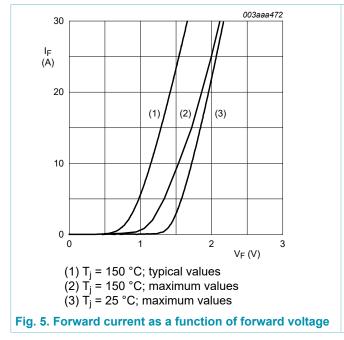
Table 6. Isolation characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V	
C _{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	pF	

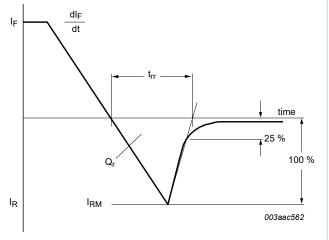
Table 5. Thermal characteristics

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10. Characteristics

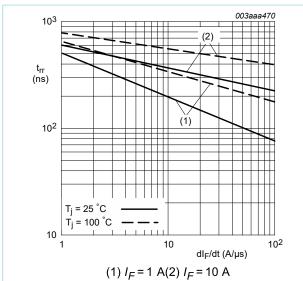
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		·			
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.75	1.95	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.07	1.5	V
		I _F = 8 A; T _j = 25 °C; <u>Fig. 5</u>	-	-	1.7	V
I _R	reverse current	V _R = 600 V; T _j = 100 °C	-	0.1	0.2	mA
		V _R = 600 V; T _j = 25 °C	-	1	10	μA
Dynamic ch	naracteristics		·			
t _{rr}	reverse recovery time	$ I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 A/\mu \text{s}; \\ T_j = 25 ^\circ\text{C}; \underline{\text{Fig. 6}}; \underline{\text{Fig. 7}} $	-	60	75	ns
I _{RM}	peak reverse recovery current	$ I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 A/\mu \text{s}; \\ T_j = 100 \ ^\circ \text{C}; \underline{\text{Fig. 6}}; \underline{\text{Fig. 8}} $	-	-	6	A
Q _r	recovered charge	$ I_F = 2 \text{ A}; \text{V}_\text{R} = 30 \text{ V}; \text{d}_\text{F}/\text{d}\text{t} = 20 \text{ A}/\mu\text{s}; \\ \text{T}_j = 25 ^\circ\text{C}; \underline{\text{Fig. 9}}; \underline{\text{Fig. 6}} $	-	150	200	nC
V _{FR}	forward recovery voltage	I _F = 10 A; dI _F /dt = 10 A/μs; T _j = 25 °C; <u>Fig. 10</u>	-	5	-	V







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maximum values

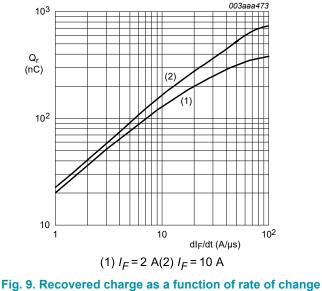
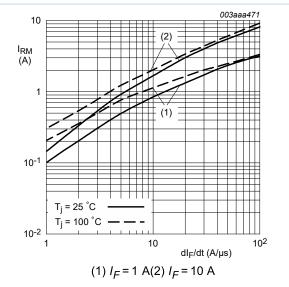
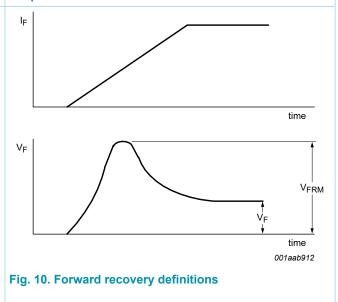


Fig. 9. Recovered charge as a function of rate of change of forward current









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11. Package outline

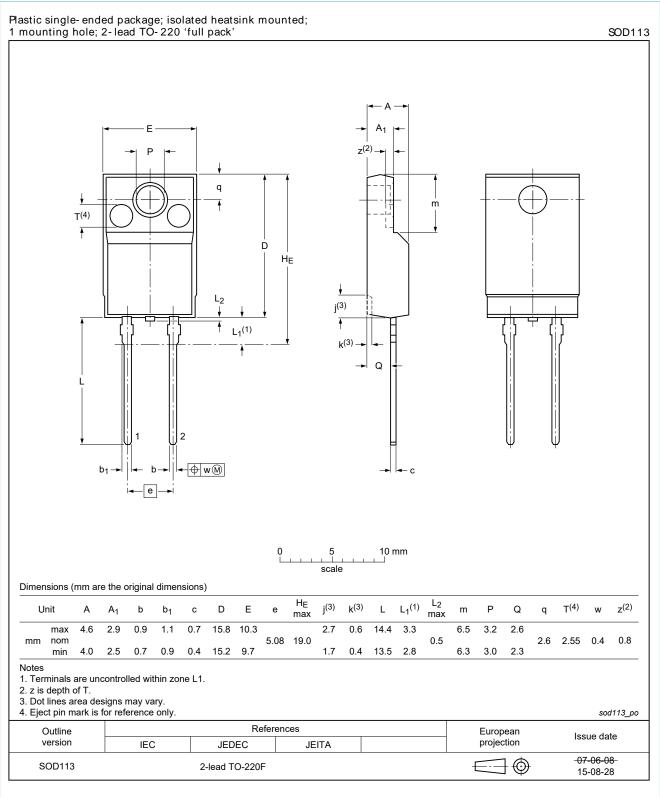


Fig. 11. Package outline TO-220F (SOD113)

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12. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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